

*Assessment of Diffusion Mobilities in
the γ' (L1₂-Ni₃Al) and B2 (NiAl)
Structures*

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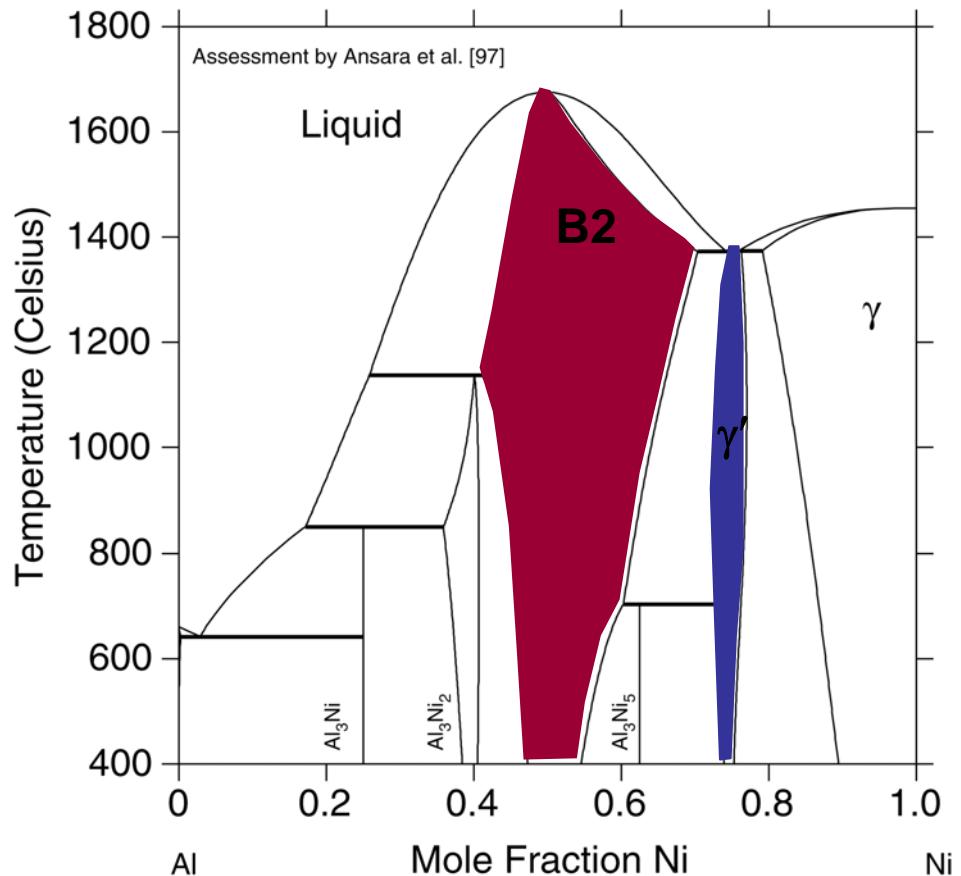
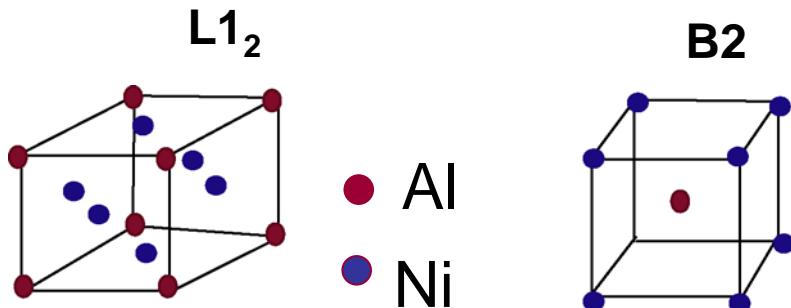
Ordered Phase in Ni-base Superalloys

B2: CsCl structure

γ' : $L1_2$ base

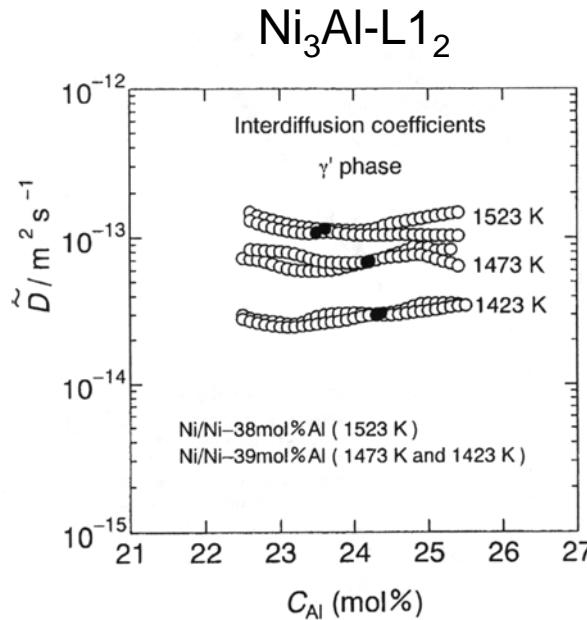
B2: Wide homogeneity range (~36 to 57 at.% Al)

Atomic mechanism: consists of several consecutive jumps

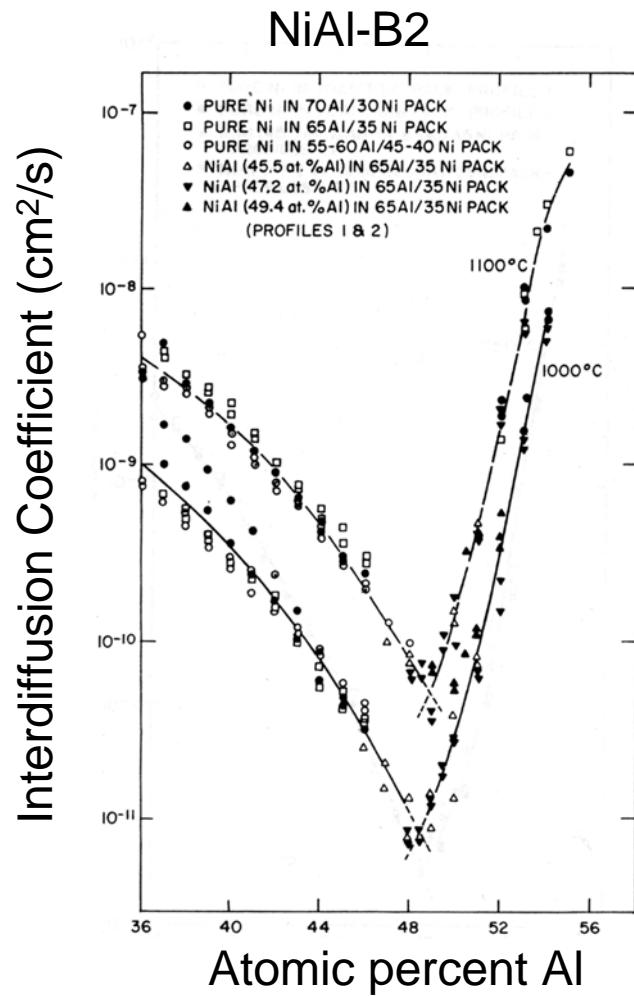


Why add ordering to diffusion model

- Strongly composition dependent diffusion coefficients (B2-NiAl)
- Phase fractions are significant; should not ignore diffusion



From Fujiwara and Horita, Acta Mater., **50** (2002) 1571.)



From Shankar and Seigle, Metall. Trans. **9A**, (1978) 1476.

Defects in Intermetallics

- 4-type of defects in A_aB_b intermetallics
 - Vacancies on both sublattices: V_A and V_B
 - Atoms on unlike sublattices A_B and B_A
 - Structural defects: defects that are present in thermal equilibrium
 - Thermal defects
- Effect of crystal structure on the self-diffusion properties of Ni_3Al -L1₂ and NiAl-B2
 - Ni_3Al : metal sublattice contains a connected network for nearest neighbor jumps for vacancies
 - NiAl: metal sublattice requires jumps between different sublattices.

Diffusion Database Development: Inputs

- Thermodynamics (CALPHAD approach)
- Diffusion experiments (unary, binary, ternary systems)
 - Tracer diffusivity,
 - Intrinsic diffusivity
 - Interdiffusion coefficients
- Define Mobility Functions
 - Composition and temperature dependent

$$M_i = \frac{M_i^\circ}{RT} \exp\left(\frac{-\Delta Q_i^*}{RT}\right) \text{ where } \Delta Q_i^* = f(c_i, T)$$

$$\Delta Q_i^* = \sum_{p=1}^n x_p Q_i^p + \sum_p^n \sum_{q>p}^n x_p x_q \left[\sum_{r=0}^m {}^r A_i^{pq} (x_p - x_q)^r \right] + \sum_p \sum_{q>p} \sum_{v>q} x_p x_q x_v [v_{pqv}^s {}^s B_i^{pqv}]$$

is exponentially dependent on composition $M_i = \frac{1}{RT} \exp\left(\frac{\Delta Q_i}{RT}\right)$

$$\Delta Q_i = \Delta Q_i^* - RT \Theta_i \quad \text{and} \quad M_i^0 = \exp(\Theta_i)$$

Effect of chemical ordering on diffusion

$$M_i = \frac{M_i^\circ}{RT} \exp\left(\frac{-\Delta Q_i}{RT}\right) \text{ where } \Delta Q_i = f(c_i, T) \text{ and } M_i^\circ = f(c_i, T)$$

- Based on Bragg-Williams approach by Girifalco for a binary system

(*J. Phys. Chem. Solids*, 1964, **24**, 323.)

$$\Delta Q_k = \Delta Q_k^{\text{dis}} \left[1 + \alpha_k (S^{\text{ord}})^2 \right] \quad S^{\text{ord}} = p_A^\alpha - p_A^\beta = \text{long-range order parameter}$$

p_A^α is the probability of finding A atom on an α site

- Expansion to Multicomponent systems Helander and Ågren, (*Acta Mater.*, 1999, **47**, 1141.)

$$\Delta Q = \Delta Q^{\text{dis}} + \Delta Q^{\text{ord}}$$

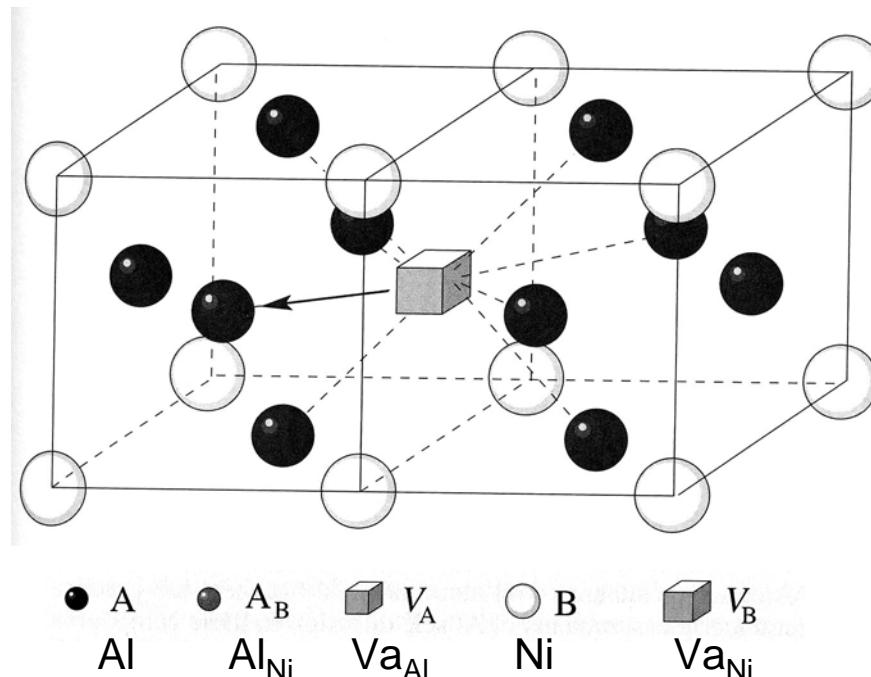
$$\begin{aligned} \Delta Q^{\text{ord}} &= \sum_i \sum_j \Delta Q_{i:j}^{\text{ord}} [y_i^\alpha y_j^\beta - x_i x_j] \\ &+ \sum_i \sum_j \sum_k \Delta Q_{ij:k}^{\text{ord}} [y_i^\alpha y_j^\alpha y_k^\beta - x_i x_j x_k] \\ &+ \sum_i \sum_j \sum_k \Delta Q_{k:ij}^{\text{ord}} [y_i^\beta y_j^\beta y_k^\alpha - x_i x_j x_k] \end{aligned}$$

$\Delta Q_{ij}^{\text{ord}}$ = contribution to activation energy for component k as a result of the ordering of $i-j$ atoms

$$y_i^\alpha = \frac{N_i^\alpha}{N_{\text{tot}}^\alpha} = p_i^\alpha$$

Ni₃Al: Diffusion Mechanism

- Sublattice diffusion mechanism
 - Random jumps of a vacancy on a sublattice do not affect the order in the compound.
 - Diffusivities of the two components are not coupled
 - Ni diffusion is expected to be faster than Al diffusion



Experimental observations

- Self-Diffusion
 - Ni Diffusion
 - Temperature dependence
 - $T > 1100$ K: Arrhenius temperature on temperature
 - $T < 1100$ K: Some experimental results show a deviation from the linear Arrhenius dependence on temperature.
 - » Frank et al. showed this deviation is due to short-circuit diffusion in polycrystalline samples
 - Composition dependence
 - Experiments indicate some minimum in $D^* \sim 76\%$ at. Ni; however, this may be due short-circuit diffusion or grain boundary diffusion effects.
 - Monte Carlo studies found a minimum at the stoichiometric composition due to the existence of Al and Ni antistructure atoms in Ni and Al rich alloys.
 - Marginal composition dependence
 - Al diffusion (limited experimental data)
 - Small composition dependence
 - $D_{Al}^*/D^* \approx 0.3$ (Ikeda 1998)
- Interdiffusion
 - Marginal composition dependence

Assessment of diffusion mobilities in Ni₃Al

- L1₂ (Ni₃Al) (Ni,Al:Ni,Al)

- Disorder description fixed

$$M_i = \frac{M_i^{\circ}}{RT} \exp\left(\frac{-\Delta Q_i^*}{RT}\right) \text{ where } \Delta Q_i^* = f(c_i, T)$$

$$\Delta Q_{Ni}^* = x_{Ni} Q_{Ni}^{Ni} + x_{Al} Q_{Al}^{Ni}$$

$$\Delta Q_{Al}^* = x_{Ni} Q_{Ni}^{Al} + x_{Al} Q_{Al}^{Al} + x_{Al} x_{Ni} Q_{Al,Ni}^{Al}$$

- Order description

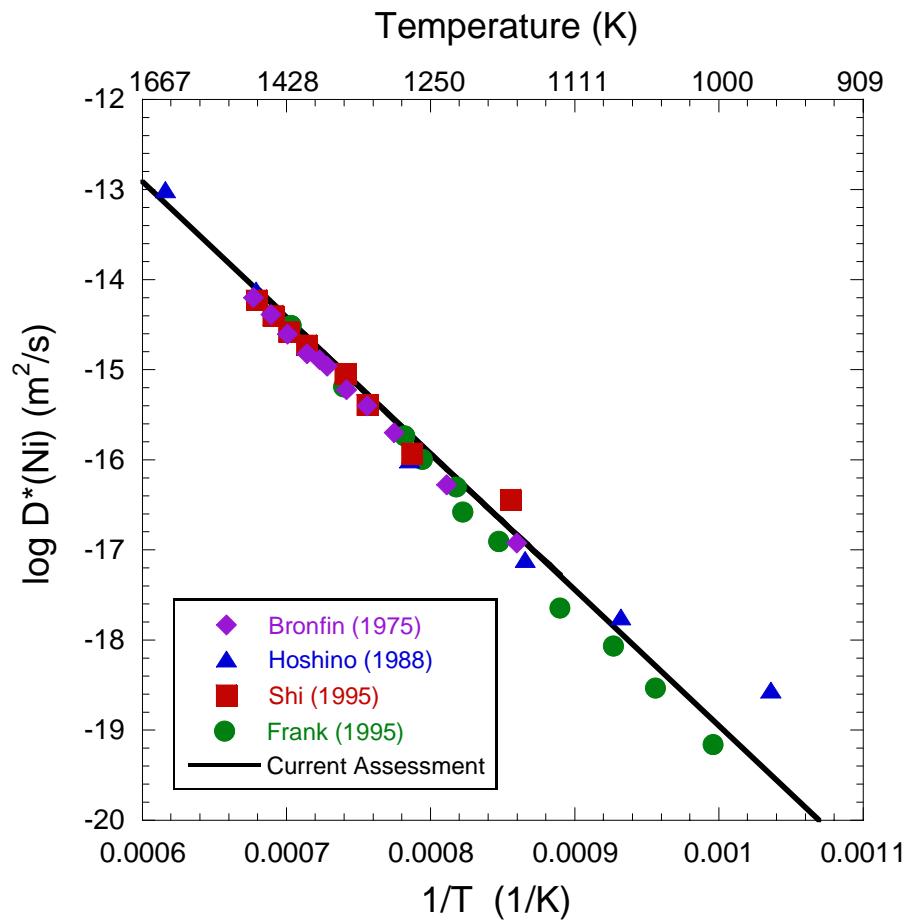
$$\begin{aligned} \Delta Q_{Ni}^{ord} &= \underline{\Delta Q_{Al:Ni}^{ord}} \left[y_{Al}^{Ni} y_{Ni}^{Al} - x_{Al} x_{Ni} \right] + \underline{\Delta Q_{Ni:Al}^{ord}} \left[y_{Ni}^{Ni} y_{Al}^{Al} - x_{Al} x_{Ni} \right] \\ &+ \underline{\Delta Q_{Al:Al}^{ord}} \left[y_{Al}^{Ni} y_{Al}^{Al} - x_{Al} x_{Al} \right] + \underline{\Delta Q_{Ni:Ni}^{ord}} \left[y_{Ni}^{Ni} y_{Ni}^{Al} - x_{Ni} x_{Ni} \right] \end{aligned}$$

$$\begin{aligned} \Delta Q_{Al}^{ord} &= \underline{\Delta Q_{Al:Ni}^{ord}} \left[y_{Al}^{Ni} y_{Ni}^{Al} - x_{Al} x_{Ni} \right] + \underline{\Delta Q_{Ni:Al}^{ord}} \left[y_{Ni}^{Ni} y_{Al}^{Al} - x_{Al} x_{Ni} \right] \\ &+ \underline{\Delta Q_{Al:Al}^{ord}} \left[y_{Al}^{Ni} y_{Al}^{Al} - x_{Al} x_{Al} \right] + \underline{\Delta Q_{Ni:Ni}^{ord}} \left[y_{Ni}^{Ni} y_{Ni}^{Al} - x_{Ni} x_{Ni} \right] \\ &+ \underline{\Delta Q_{Al,Ni:Al}^{ord}} \left[y_{Al}^{Ni} y_{Ni}^{Ni} y_{Al}^{Al} - x_{Al} x_{Ni} x_{Al} \right] \\ &+ \underline{\Delta Q_{Al,Ni:Ni}^{ord}} \left[y_{Al}^{Ni} y_{Ni}^{Ni} y_{Ni}^{Al} - x_{Al} x_{Ni} x_{Ni} \right] \end{aligned}$$

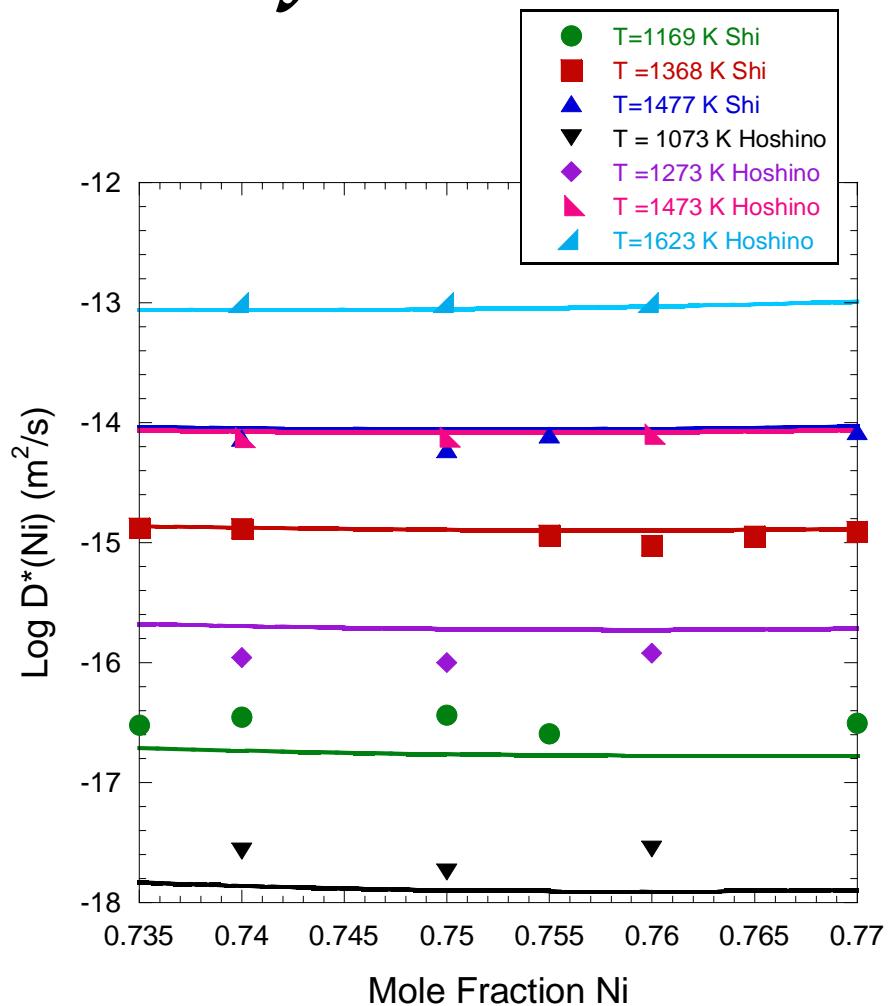
Assessed Mobility Parameters

Mobility Parameters	Value
Ni	
$\Delta Q_{Ni:Al} = \Delta Q_{Ni:Al}$	-87723-58.15*T
$\Delta Q_{Al:Al}$	57853
$\Delta Q_{Ni:Ni}^{ord}$	-889101
Al	
$\Delta Q_{Ni:Al} = \Delta Q_{Ni:Al}$	2255-20.22*T
$\Delta Q_{Al:Al}$	-268884
$\Delta Q_{Ni:Ni}^{ord}$	84356
$\Delta Q_{Al,Ni:Al}^{ord} = \Delta Q_{Al,Ni:Ni}^{ord}$	2333274

Self Diffusion of Ni



Arrhenius temperature dependence

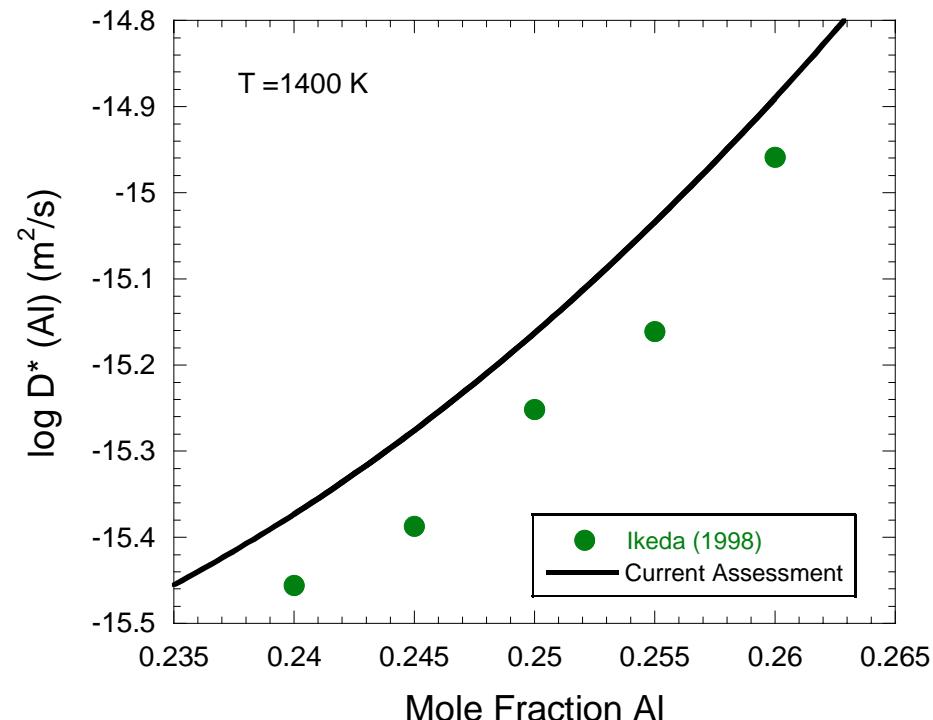
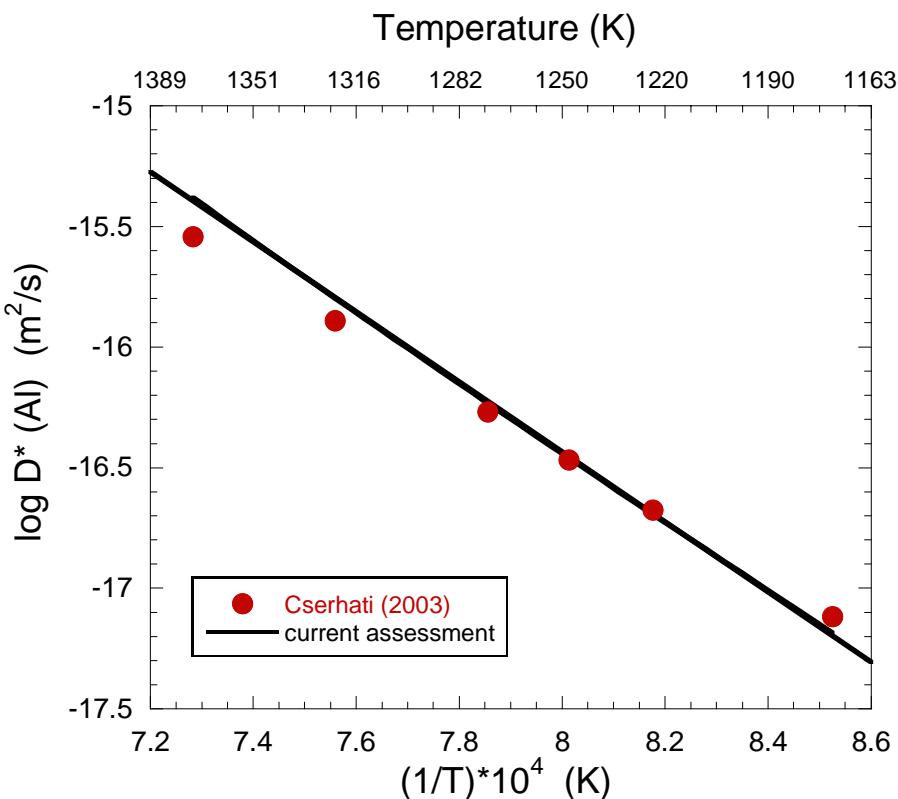


Small Composition dependence

Self-Diffusion of Al

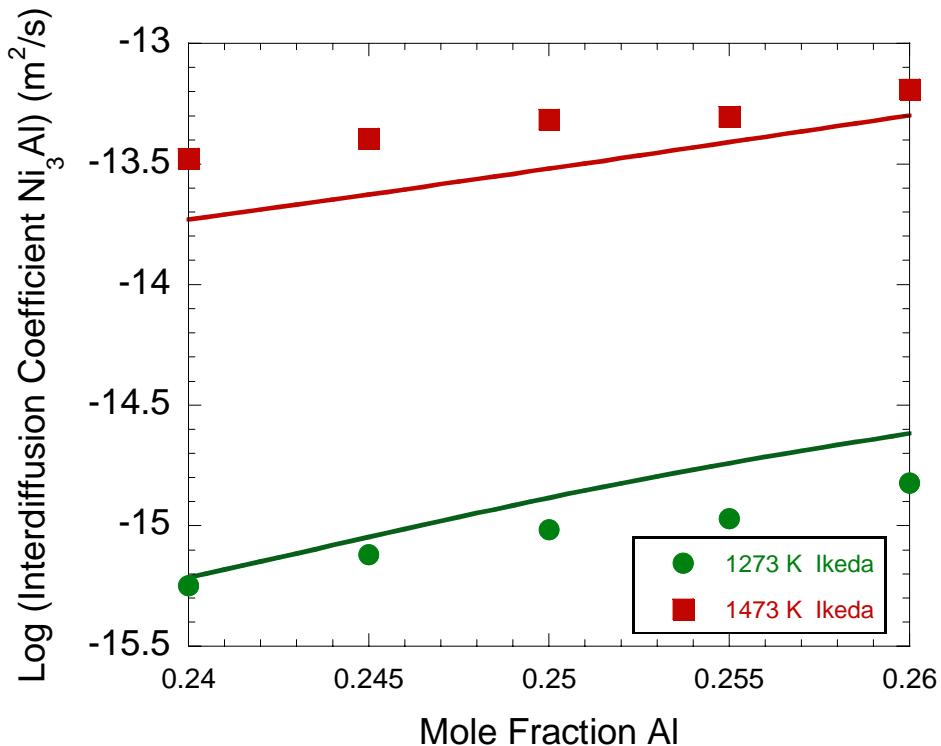
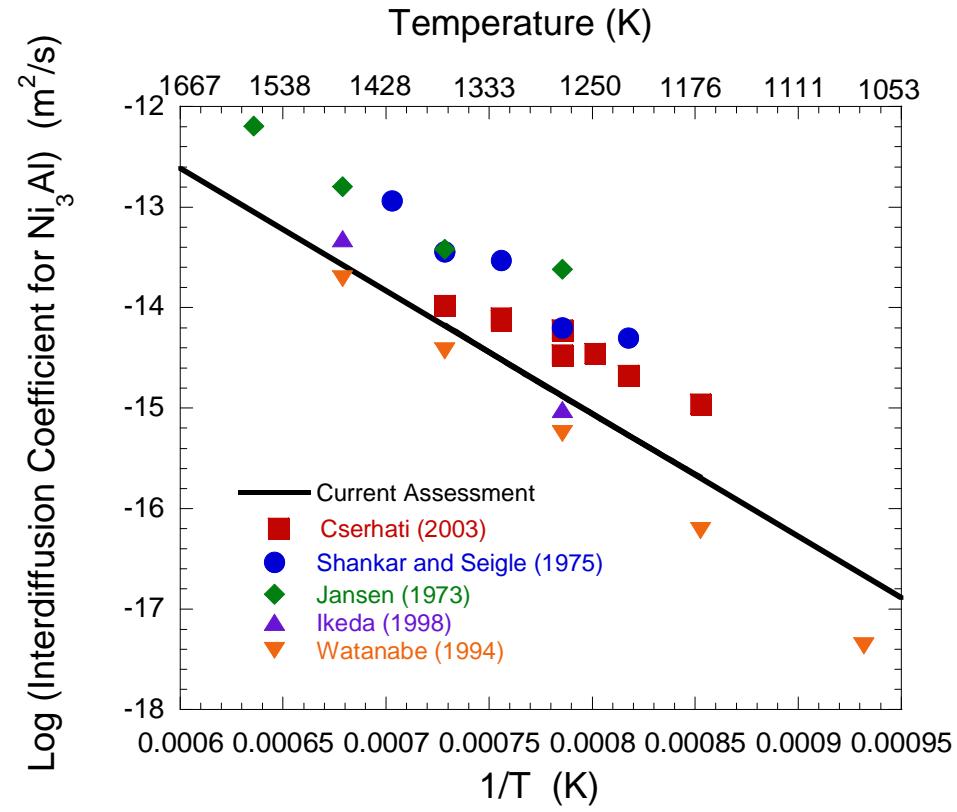
Experimental D^*_{Al} is determined from \tilde{D}_{Ni_3Al} using the Darken-Manning eqn.

$$\tilde{D} = (x_{Al} D^*_{Ni} + x_{Ni} D^*_{Al}) \cdot \Phi \cdot S$$

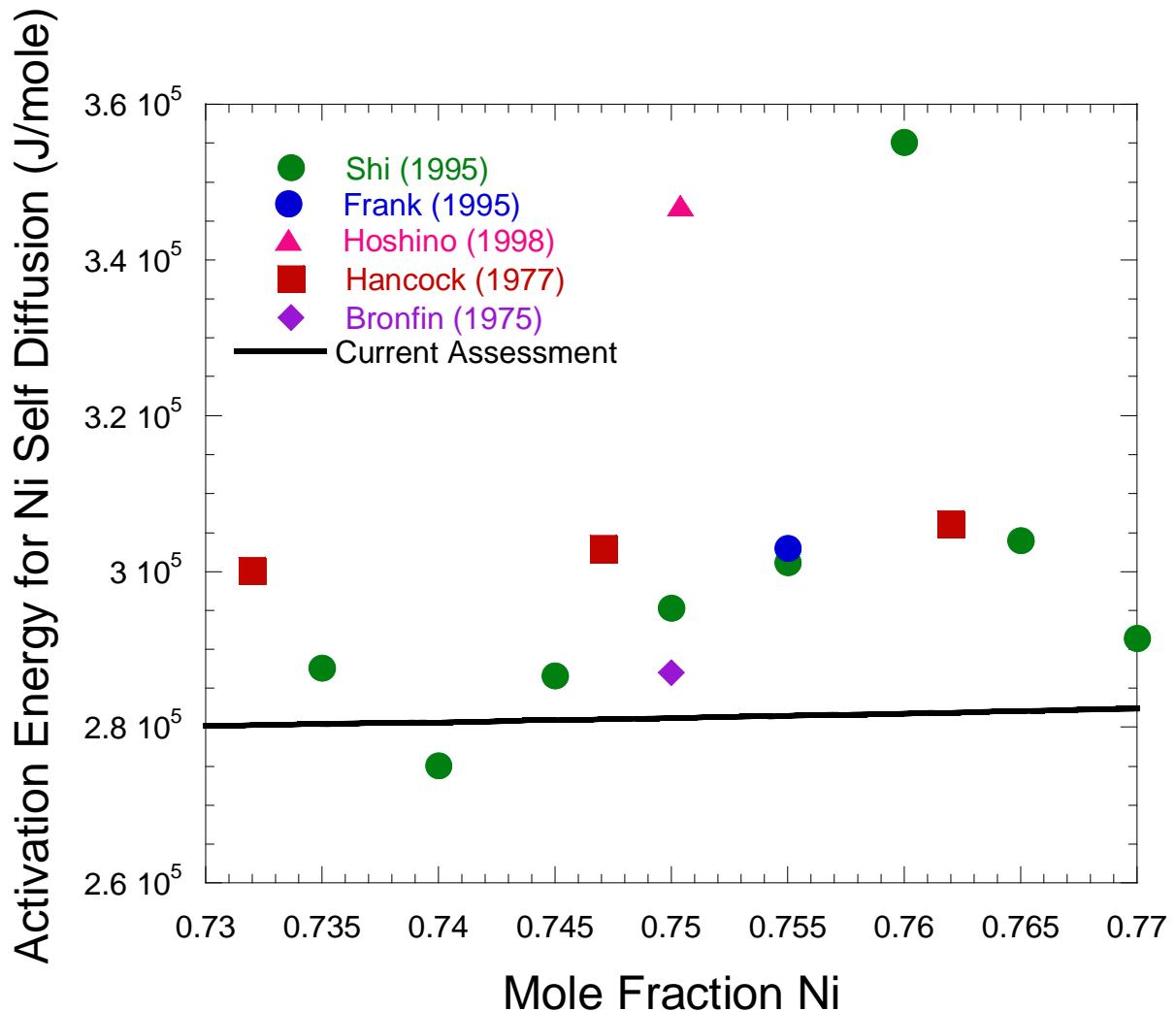


D^*_{Al} increases by a factor of 3
for a 3 percent change in Al

Interdiffusion Data



Activation Energy



NiAl-B2 Crystal Structure

- 2 penetrating simple cubic lattices
 - Al atoms occupy the corners of one sublattice
 - Ni atoms occupy the corners of the other sublattice.
- Different defect structures on either side of the stoichiometric composition
 - Al-rich side: excess Ni atoms occupy Al lattice sites
→ anti-structure defects and structural Ni vacancies
 - Ni-rich side: structural vacancies

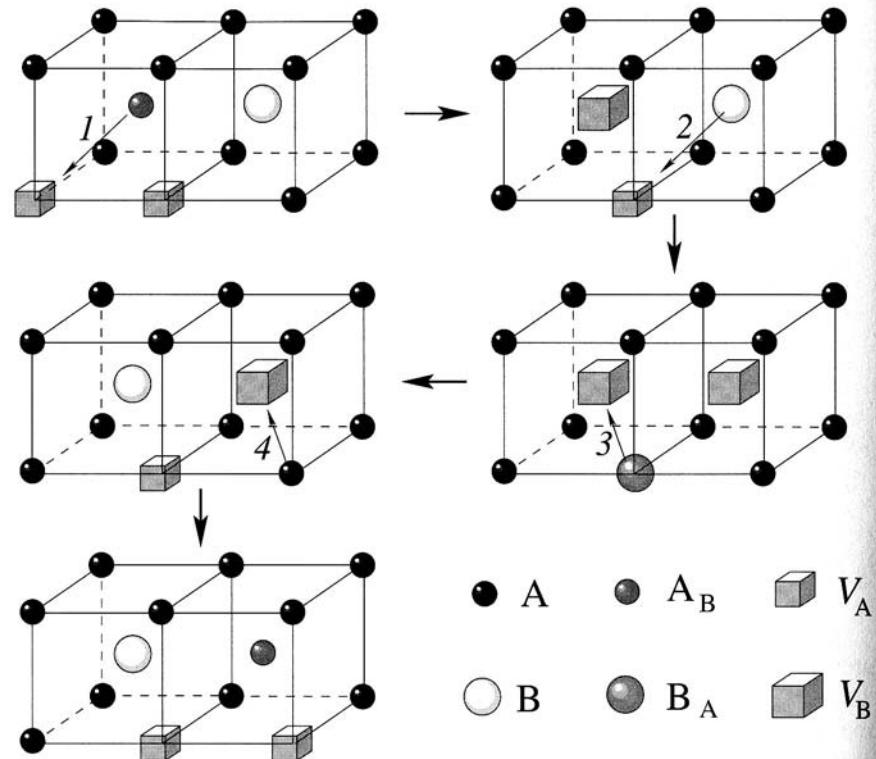
Experimental Observations

- Ni-Self Diffusion
 - Temperature dependence: $T > 1500$ K upward deviation from Arrhenius dependence.
 - Composition dependence:
 - On Al-rich side, structural Ni-vacancies do not increase diffusivity (Frank et. al. 2001)
 - Ni-rich side: increasing diffusivity
 - Activation energy
 - Constant from 46.5 to 53 at.% Ni
 - Decreasing for Ni>53 at.%
- Al-Self Diffusion
 - No direct measurements
 - Significant composition dependence deduced from interdiffusion coefficient measurements (deep minimum at stoichiometric composition)
 - Dependent on presence of V_{Ni}

Diffusion Mechanisms in NiAl-B2

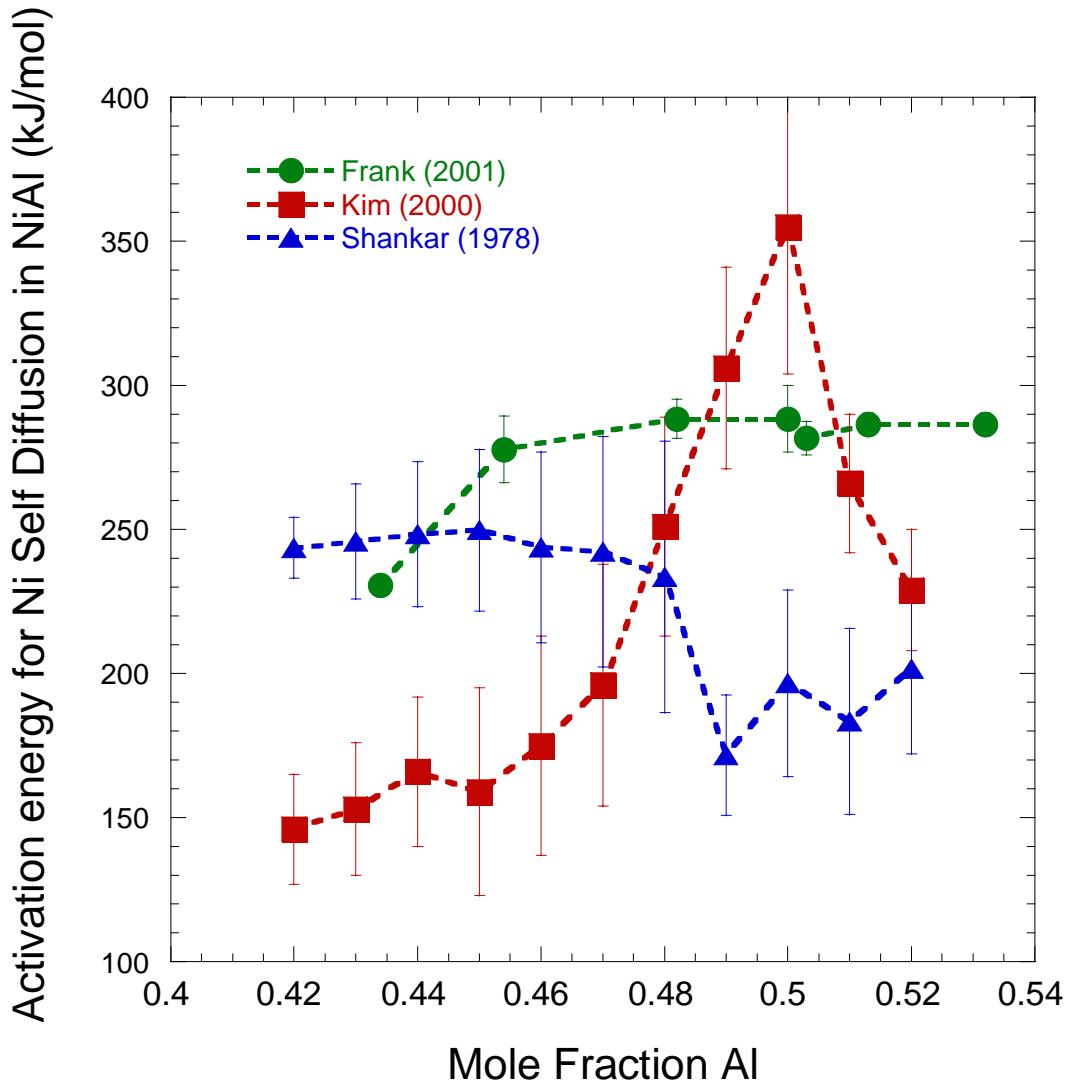
- All nearest neighbor jumps are jumps between different sublattices
- Ni vacancies on the Al-rich side significantly affect the Ni self-diffusion
- Active diffusion mechanisms:
 - Triple-defect mechanism ($2 V_{Ni} N_{Al}$)
 - Composition independent activation energy ($\sim 300 \text{ kJ/mol}$)
 - Anti-structure Bridge Mechanism (ASB)
 - Percolation effect (threshold > 55.5 at.% Ni)
 - Next nearest neighbor jumps of Ni atoms
 - Lower temperatures in Al-rich compositions

Triple Defect Mechanism in a NiAl-B2 Structure



From Frank et al. Acta Mater. 2001

Activation Energy

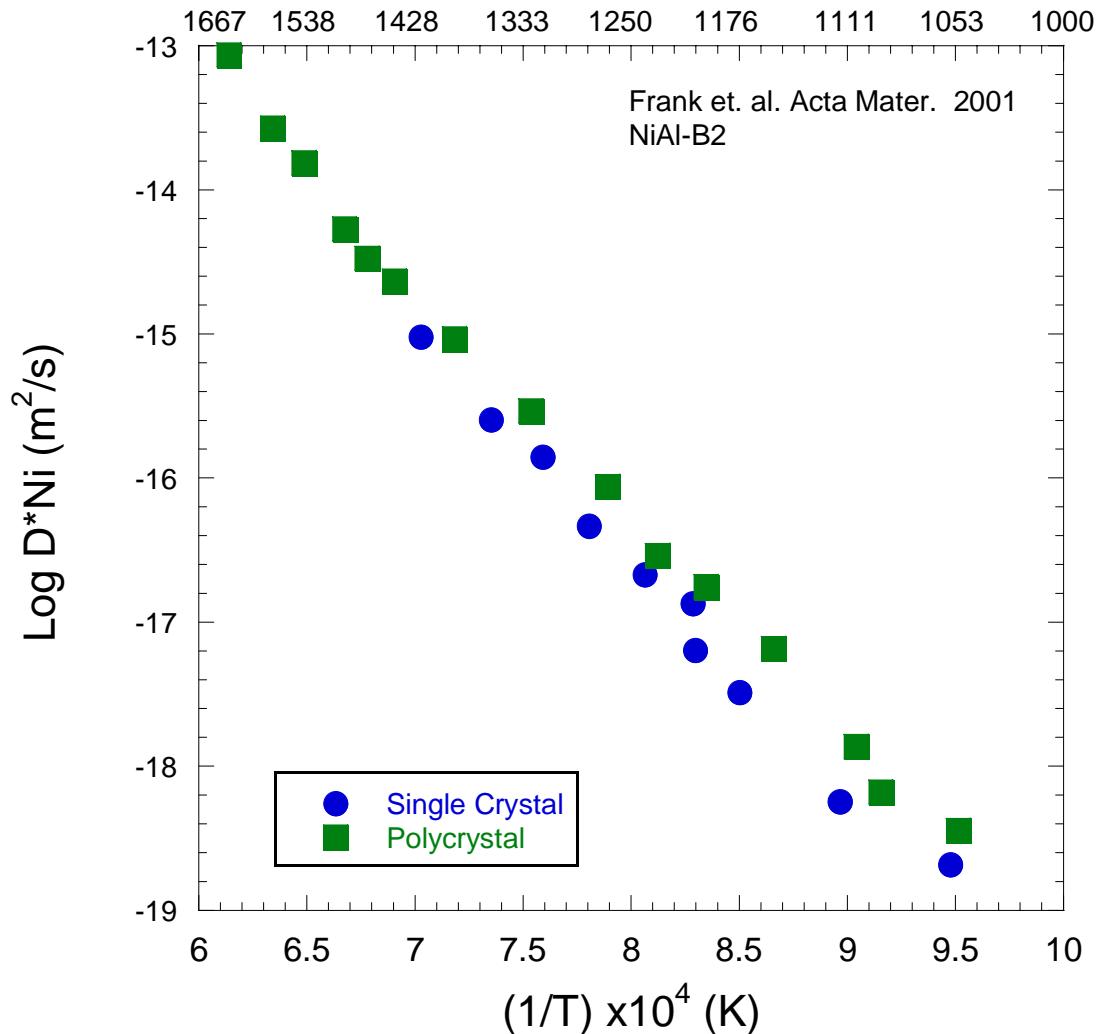


Why so much disagreement?

- Grain boundary diffusion
- Annealing treatment: high temperatures may result in quenched in vacancies that are not in thermodynamic equilibrium
- Kim and Chang used lattice-mole fraction

Temperature Dependence of Ni Self-Diffusion in NiAl

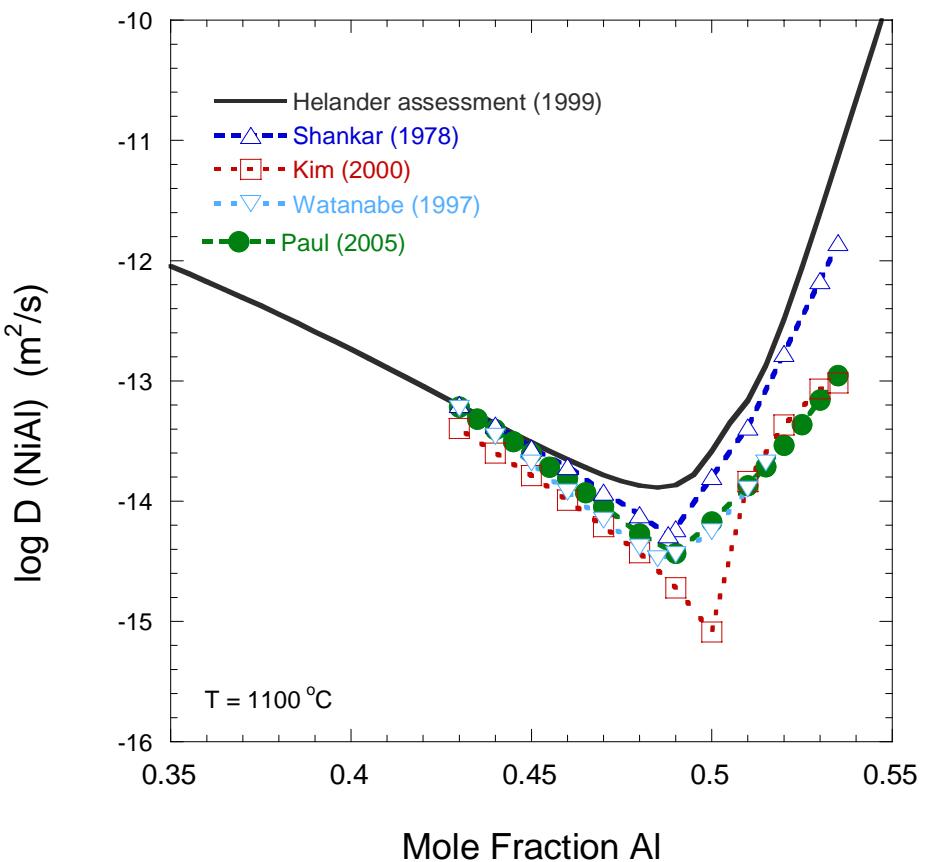
Temperature (K)



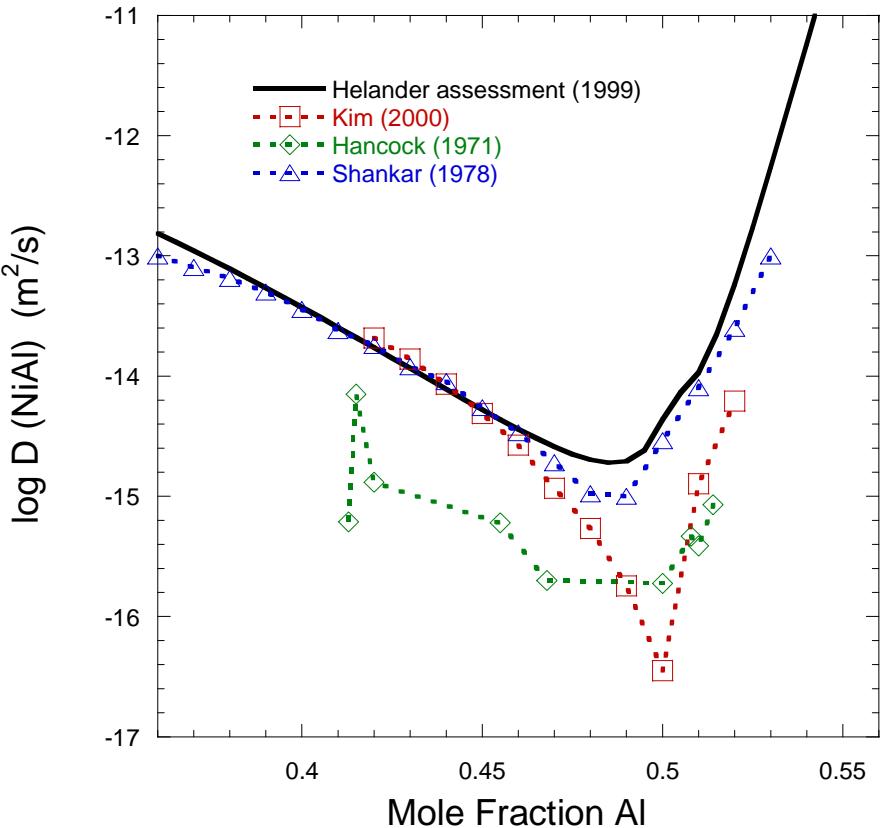
Similar results on
the Ni-rich and Al-
rich compositions

Diffusion in B2-NiAl

NiAl (B2) at 1100 °C



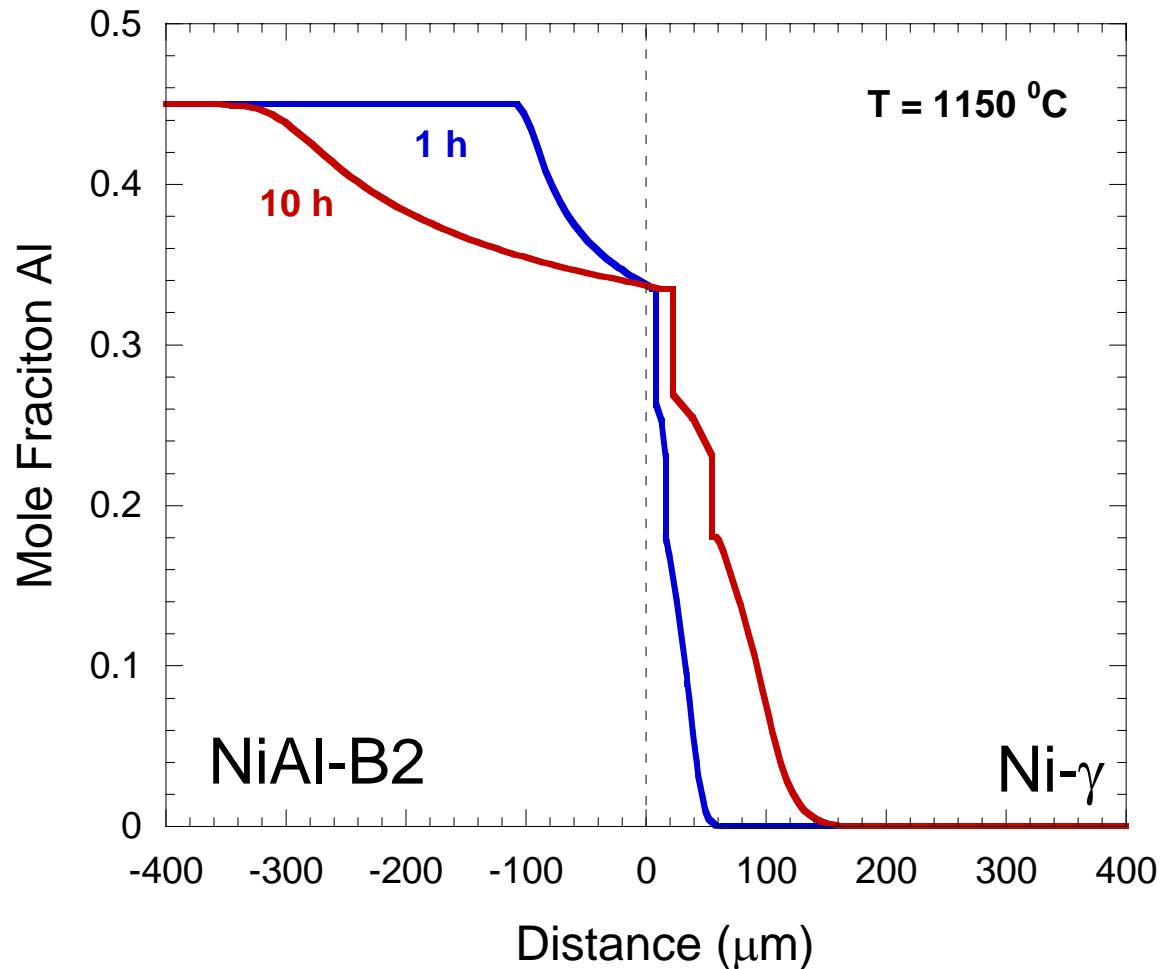
NiAl (B2) at 1000 °C



Features the B2 model must reproduce

- Activation energy
 - Does not depend on composition in the range $0.46 < x_{\text{Ni}} < 0.53$: constant $\approx 290 \text{ kJ/mol}$
 - Decreases with increasing Ni for $x_{\text{Ni}} > 0.53$
- Ni self diffusion
 - Ni-rich side ($0.5 < x_{\text{Ni}} < 0.53$): increases with increasing Ni composition
 - Al-rich side ($0.46 < x_{\text{Ni}} < 0.50$): remains constant with increasing Ni composition

Example: NiAl/Ni at 1150 °C



Summary

- Order diffusion model developed by Helandar and Agren successfully applied to Ni₃Al.
- Order diffusion modeling of NiAl-B₂ is a greater challenge
 - Need to incorporate vacancies on sublattice model
 - *Does the Darken-Manning eq hold?*